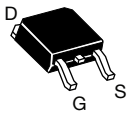
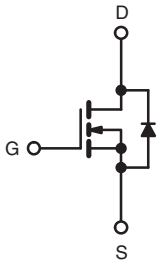
# D Series Power MOSFET

| PRODUCT SUMMARY | | |
|---|---|---|
| $V_{DS}$ (V) at $T_J$ max. | 550 | |
| $R_{DS(on)}$ max. at 25 °C (Ω) | $V_{GS}$ = 10 V | 1.5 |
| $Q_g$ (max.) (nC) | 20 | |
| $Q_{gs}$ (nC) | 3 | |
| $Q_{gd}$ (nC) | 5 | |
| Configuration | Single | |

**DPAK (TO-252)**




N-Channel MOSFET

## FEATURES

- Optimal Design
  - Low Area Specific On-Resistance
  - Low Input Capacitance ($C_{iss}$)
  - Reduced Capacitive Switching Losses
  - High Body Diode Ruggedness
  - Avalanche Energy Rated (UIS)
- Optimal Efficiency and Operation
  - Low Cost
  - Simple Gate Drive Circuitry
  - Low Figure-of-Merit (FOM): $R_{on}$ x $Q_g$
  - Fast Switching
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

RoHS COMPLIANT
HALOGEN FREE Available

## APPLICATIONS

- Consumer Electronics
  - Displays (LCD or Plasma TV)
- Server and Telecom Power Supplies
  - SMPS
- Industrial
  - Welding
  - Induction Heating
  - Motor Drives
- Battery Chargers

| ORDERING INFORMATION | |
|---|---|
| Package | DPAK (TO-252) |
| Lead (Pb)-free | SiHD5N50D-E3 |
| Lead (Pb)-free and Halogen-free | SiHD5N50D-GE3 |
| | SiHD5N50DT1-GE3 |
| | SiHD5N50DT4-GE3 |
| | SiHD5N50DT5-GE3 |

**ABSOLUTE MAXIMUM RATINGS** ($T_C$ = 25 °C, unless otherwise noted)

| PARAMETER | | | SYMBOL | LIMIT | UNIT |
|---|---|---|---|---|---|
| Drain-Source Voltage | | | $V_{DS}$ | 500 | V |
| Gate-Source Voltage | | | $V_{GS}$ | ± 30 | |
| Gate-Source Voltage AC (f > 1 Hz) | | | | 30 | |
| Continuous Drain Current ($T_J$ = 150 °C) | $V_{GS}$ at 10 V | $T_C$ = 25 °C | $I_D$ | 5.3 | A |
| | | $T_C$ = 100 °C | | 3.4 | |
| Pulsed Drain Current[a] | | | $I_{DM}$ | 10 | |
| Linear Derating Factor | | | | 0.83 | W/°C |
| Single Pulse Avalanche Energy[b] | | | $E_{AS}$ | 23 | mJ |
| Maximum Power Dissipation | | | $P_D$ | 104 | W |
| Operating Junction and Storage Temperature Range | | | $T_J$, $T_{stg}$ | - 55 to + 150 | °C |
| Drain-Source Voltage Slope | $T_J$ = 125 °C | | dV/dt | 24 | V/ns |
| Reverse Diode dV/dt [d] | | | | 0.28 | |
| Soldering Recommendations (Peak Temperature)[c] | for 10 s | | | 300 | °C |

**Notes**

a. Repetitive rating; pulse width limited by maximum junction temperature.
b. $V_{DD}$ = 50 V, starting $T_J$ = 25 °C, L = 2.3 mH, $R_g$ = 25 Ω, $I_{AS}$ = 4.5 A.
c. 1.6 mm from case.
d. $I_{SD} \leq I_D$, starting $T_J$ = 25 °C.

## THERMAL RESISTANCE RATINGS

| PARAMETER | SYMBOL | TYP. | MAX. | UNIT |
|---|---|---|---|---|
| Maximum Junction-to-Ambient | $R_{thJA}$ | - | 62 | °C/W |
| Maximum Junction-to-Case (Drain) | $R_{thJC}$ | - | 1.2 | |

## SPECIFICATIONS ($T_J$ = 25 °C, unless otherwise noted)

| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|---|---|---|---|---|---|---|
| **Static** | | | | | | |
| Drain-Source Breakdown Voltage | $V_{DS}$ | $V_{GS}$ = 0 V, $I_D$ = 250 µA | 500 | - | - | V |
| $V_{DS}$ Temperature Coefficient | $\Delta V_{DS}/T_J$ | Reference to 25 °C, $I_D$ = 250 µA | - | 0.58 | - | V/°C |
| Gate-Source Threshold Voltage (N) | $V_{GS(th)}$ | $V_{DS}$ = $V_{GS}$, $I_D$ = 250 µA | 3 | - | 5 | V |
| Gate-Source Leakage | $I_{GSS}$ | $V_{GS}$ = ± 30 V | - | - | ± 100 | nA |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$ = 500 V, $V_{GS}$ = 0 V | - | - | 1 | µA |
| | | $V_{DS}$ = 400 V, $V_{GS}$ = 0 V, $T_J$ = 125 °C | - | - | 10 | |
| Drain-Source On-State Resistance | $R_{DS(on)}$ | $V_{GS}$ = 10 V, $I_D$ = 2.5 A | - | 1.2 | 1.5 | Ω |
| Forward Transconductance[a] | $g_{fs}$ | $V_{DS}$ = 20 V, $I_D$ = 2.5 A | - | 1.8 | - | S |
| **Dynamic** | | | | | | |
| Input Capacitance | $C_{iss}$ | $V_{GS}$ = 0 V, $V_{DS}$ = 100 V, f = 1 MHz | - | 325 | - | pF |
| Output Capacitance | $C_{oss}$ | | - | 34 | - | |
| Reverse Transfer Capacitance | $C_{rss}$ | | - | 6 | - | |
| Effective Output Capacitance, Energy Related[b] | $C_{o(er)}$ | $V_{DS}$ = 0 V to 400 V, $V_{GS}$ = 0 V | - | 31 | - | |
| Effective Output Capacitance, Time Related[c] | $C_{o(tr)}$ | | - | 41 | - | |
| Total Gate Charge | $Q_g$ | $V_{GS}$ = 10 V, $I_D$ = 2.5 A, $V_{DS}$ = 400 V | - | 10 | 20 | nC |
| Gate-Source Charge | $Q_{gs}$ | | - | 3 | - | |
| Gate-Drain Charge | $Q_{gd}$ | | - | 5 | - | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD}$ = 400 V, $I_D$ = 2.5 A, $R_g$ = 9.1 Ω, $V_{GS}$ = 10 V | - | 12 | 24 | ns |
| Rise Time | $t_r$ | | - | 11 | 22 | |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 14 | 28 | |
| Fall Time | $t_f$ | | - | 11 | 22 | |
| Gate Input Resistance | $R_g$ | f = 1 MHz, open drain | - | 1.7 | - | Ω |
| **Drain-Source Body Diode Characteristics** | | | | | | |
| Continuous Source-Drain Diode Current | $I_S$ | MOSFET symbol showing the integral reverse P - N junction diode  | - | - | 5 | A |
| Pulsed Diode Forward Current | $I_{SM}$ | | - | - | 20 | |
| Diode Forward Voltage | $V_{SD}$ | $T_J$ = 25 °C, $I_S$ = 4 A, $V_{GS}$ = 0 V | - | - | 1.2 | V |
| Reverse Recovery Time | $t_{rr}$ | $T_J$ = 25 °C, $I_F$ = $I_S$ = 2.5 A, dI/dt = 100 A/µs, $V_R$ = 20 V | - | 320 | - | ns |
| Reverse Recovery Charge | $Q_{rr}$ | | - | 1.2 | - | µC |
| Reverse Recovery Current | $I_{RRM}$ | | - | 8 | - | A |

**Notes**

a. Repetitive rating; pulse width limited by maximum junction temperature.
b. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as $C_{oss}$ while $V_{DS}$ is rising from 0 % to 80 % $V_{DSS}$.
c. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as $C_{oss}$ while $V_{DS}$ is rising from 0 % to 80 % $V_{DSS}$.

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

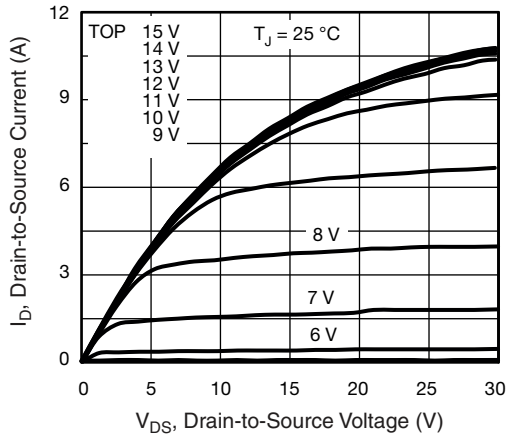



**Fig. 1 - Typical Output Characteristics**

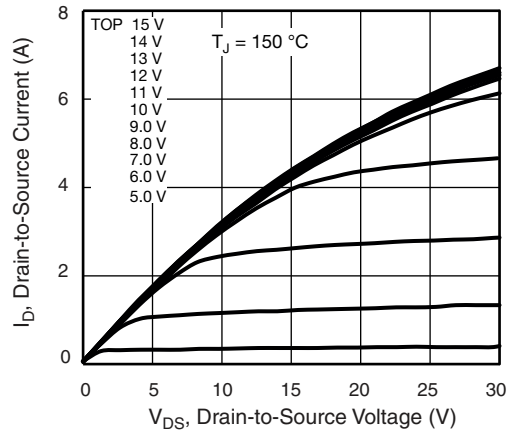



**Fig. 2 - Typical Output Characteristics**

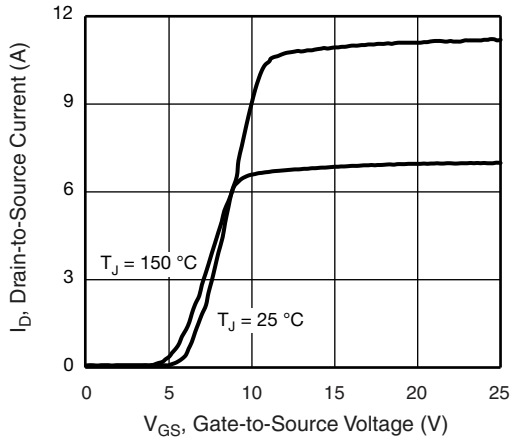



**Fig. 3 - Typical Transfer Characteristics**

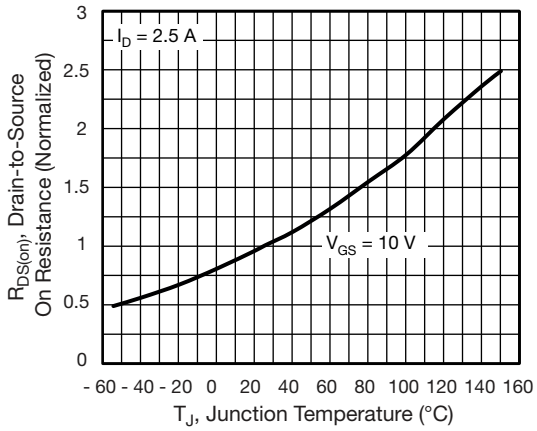



**Fig. 4 - Normalized On-Resistance vs. Temperature**

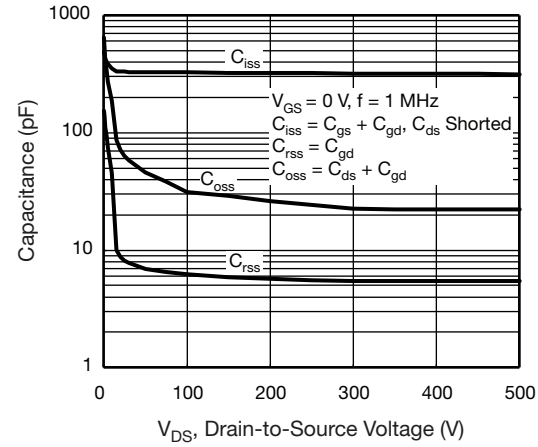



**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**

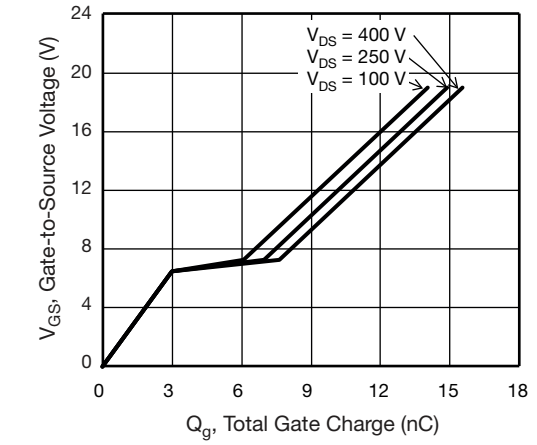



**Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage**

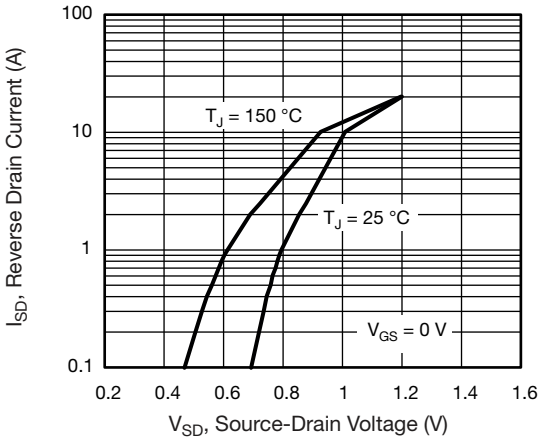



**Fig. 7 - Typical Source-Drain Diode Forward Voltage**

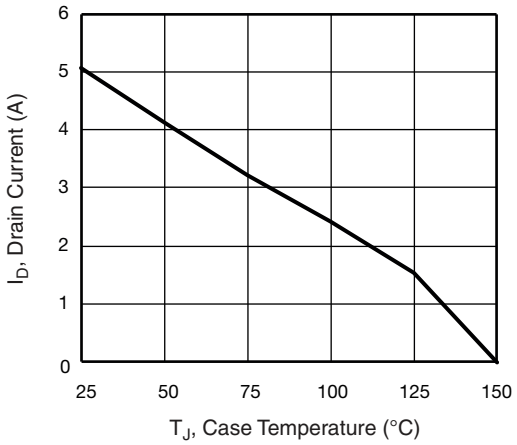



**Fig. 9 - Maximum Drain Current vs. Case Temperature**

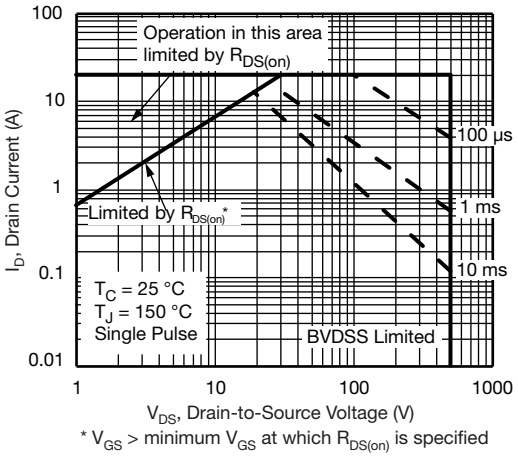



**Fig. 8 - Maximum Safe Operating Area**

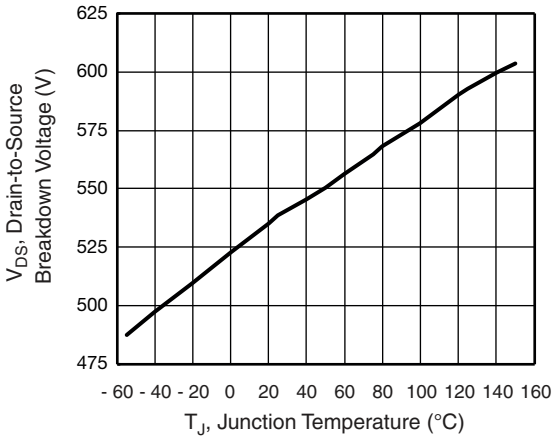



**Fig. 10 - Typical Drain-to-Source Voltage vs. Temperature**

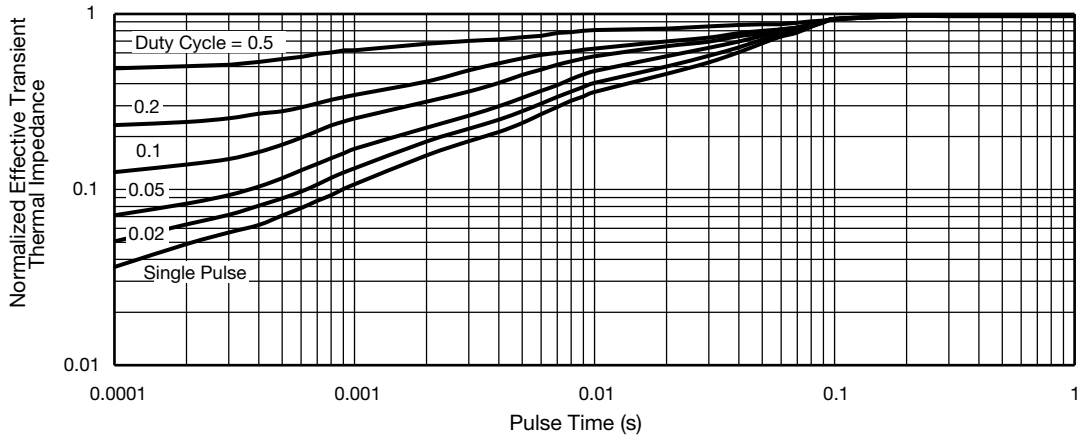



**Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case**

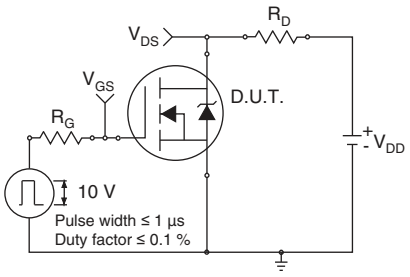



**Fig. 12 - Switching Time Test Circuit**

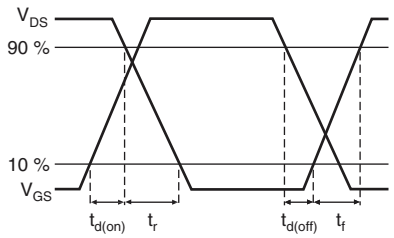



**Fig. 13 - Switching Time Waveforms**

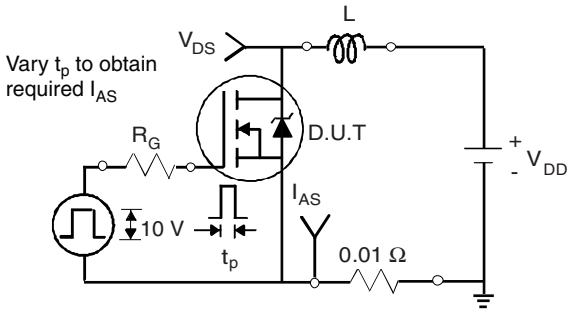



**Fig. 14 - Unclamped Inductive Test Circuit**

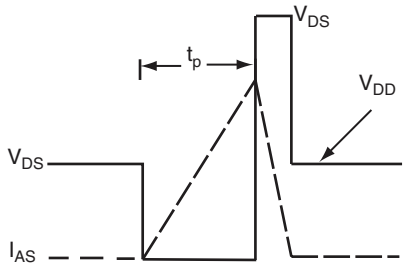



**Fig. 15 - Unclamped Inductive Waveforms**

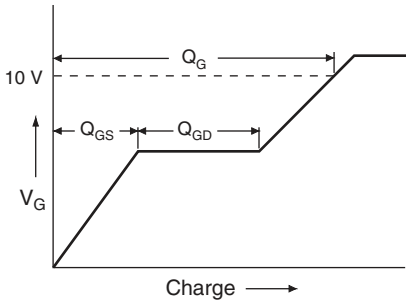



**Fig. 16 - Basic Gate Charge Waveform**

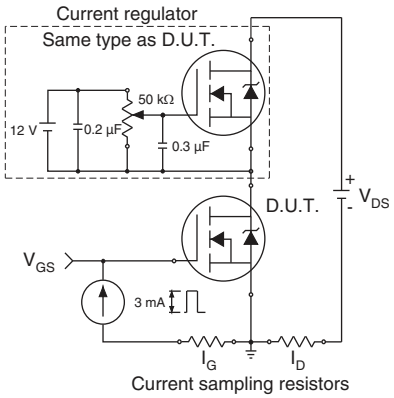
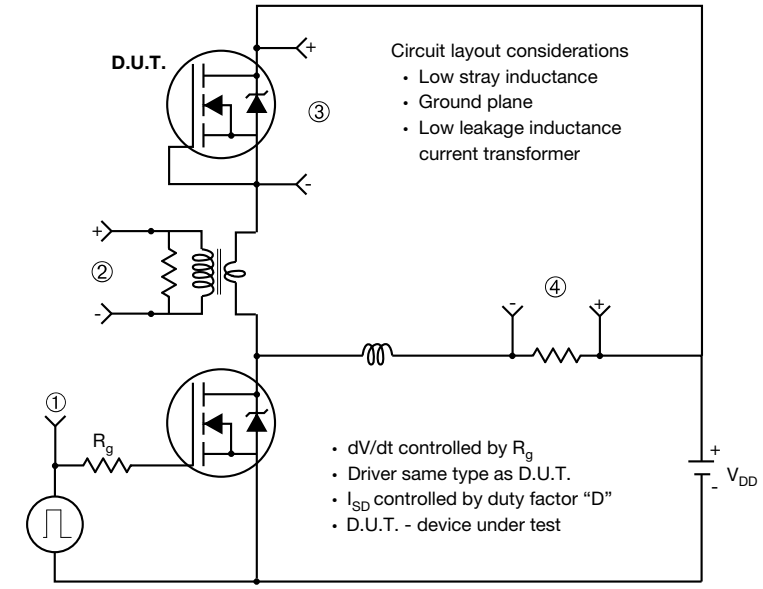
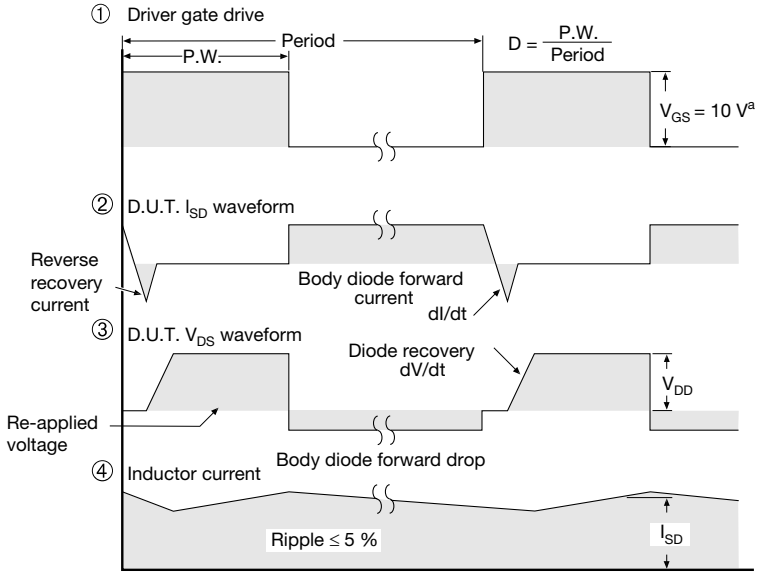



**Fig. 17 - Gate Charge Test Circuit**

**Peak Diode Recovery dV/dt Test Circuit**



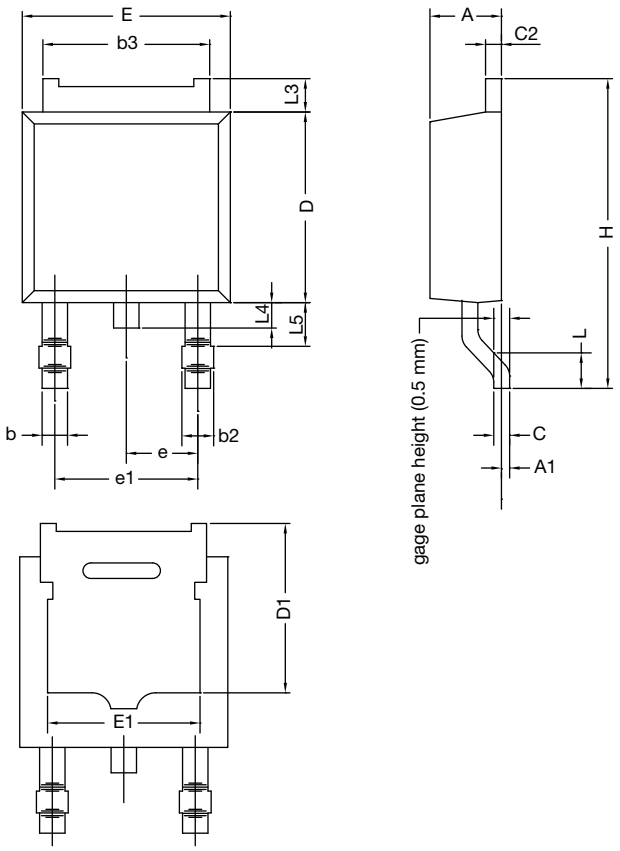




**Note**

a. $V_{GS}$ = 5 V for logic level devices

**Fig. 18 - For N-Channel**

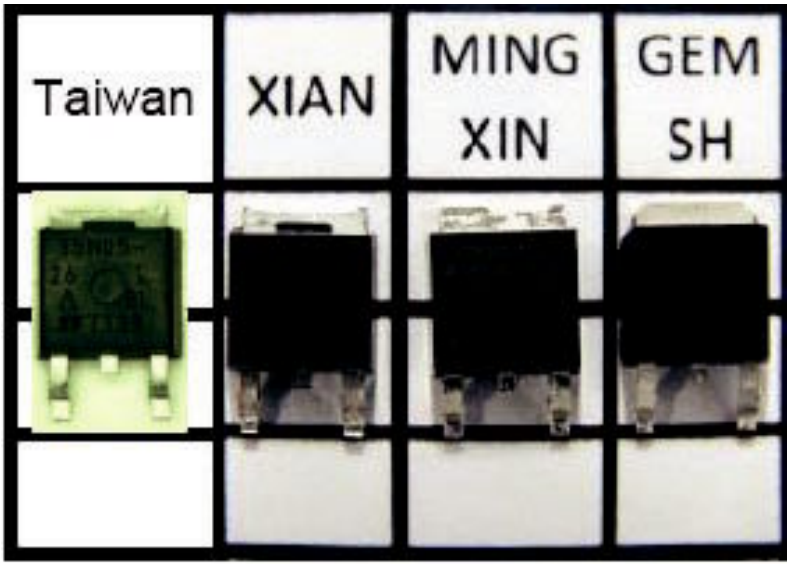
# TO-252AA Case Outline



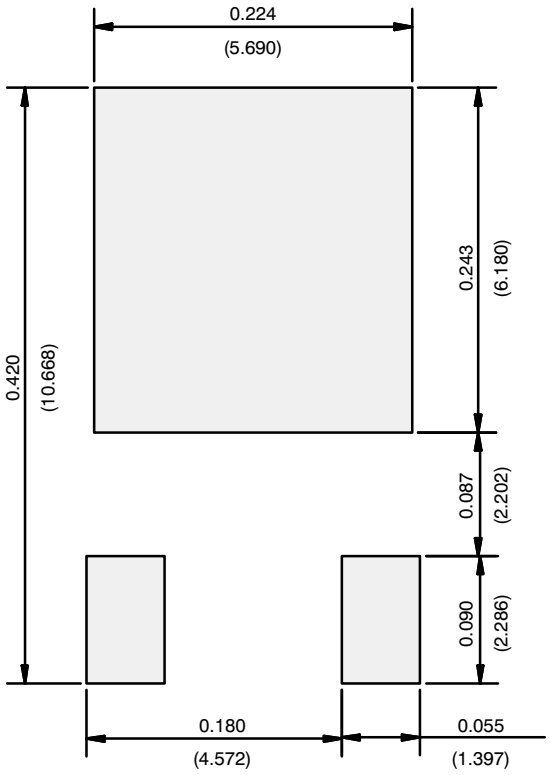

| | MILLIMETERS | | INCHES | |
|---|---|---|---|---|
| DIM. | MIN. | MAX. | MIN. | MAX. |
| A | 2.18 | 2.38 | 0.086 | 0.094 |
| A1 | - | 0.127 | - | 0.005 |
| b | 0.64 | 0.88 | 0.025 | 0.035 |
| b2 | 0.76 | 1.14 | 0.030 | 0.045 |
| b3 | 4.95 | 5.46 | 0.195 | 0.215 |
| C | 0.46 | 0.61 | 0.018 | 0.024 |
| C2 | 0.46 | 0.89 | 0.018 | 0.035 |
| D | 5.97 | 6.22 | 0.235 | 0.245 |
| D1 | 4.10 | - | 0.161 | - |
| E | 6.35 | 6.73 | 0.250 | 0.265 |
| E1 | 4.32 | - | 0.170 | - |
| H | 9.40 | 10.41 | 0.370 | 0.410 |
| e | 2.28 BSC | | 0.090 BSC | |
| e1 | 4.56 BSC | | 0.180 BSC | |
| L | 1.40 | 1.78 | 0.055 | 0.070 |
| L3 | 0.89 | 1.27 | 0.035 | 0.050 |
| L4 | - | 1.02 | - | 0.040 |
| L5 | 1.01 | 1.52 | 0.040 | 0.060 |
| ECN: T13-0359-Rev. O, 03-Jun-13<br>DWG: 5347 | | | | |

**Notes**

- Dimension L3 is for reference only.
- Xi'an, Mingxin, and GEM SH actual photo.



## RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)




Recommended Minimum Pads
Dimensions in Inches/(mm)

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